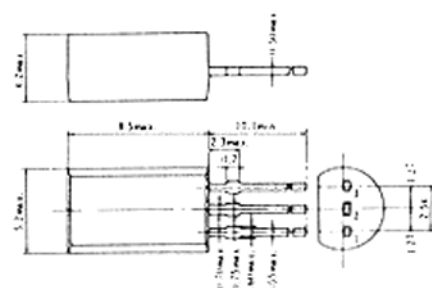


2SD2063

SILICON NPN EPITAXIAL

LOW FREQUENCY AMPLIFIER



1. Emitter
2. Collector
3. Base

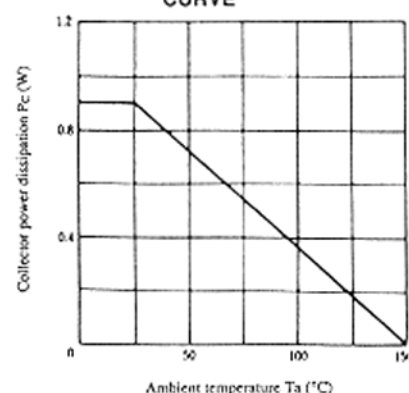
(Dimensions in mm)

(JEDEC TO-92 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

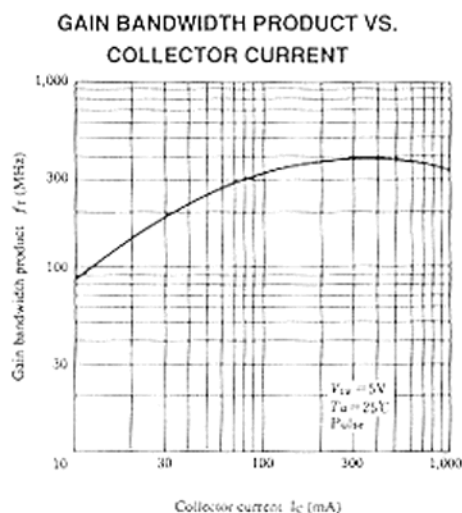
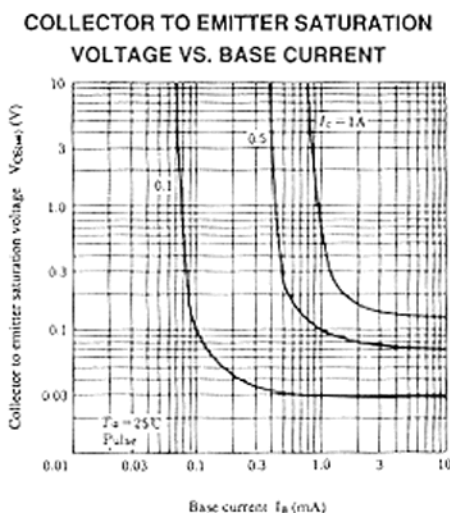
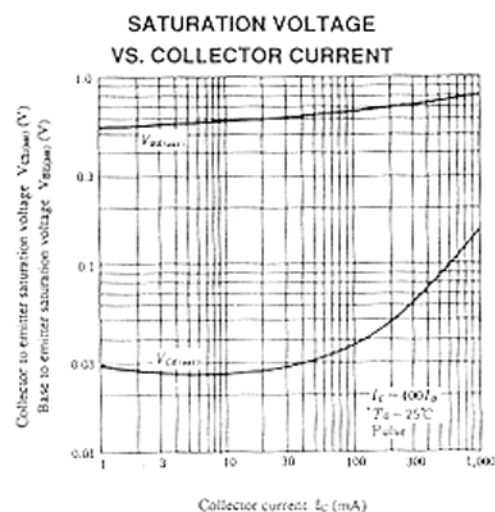
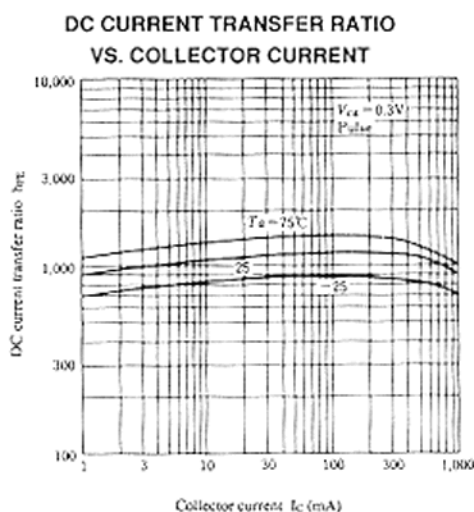
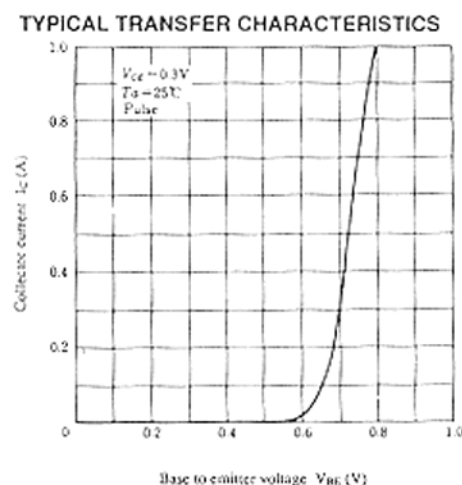
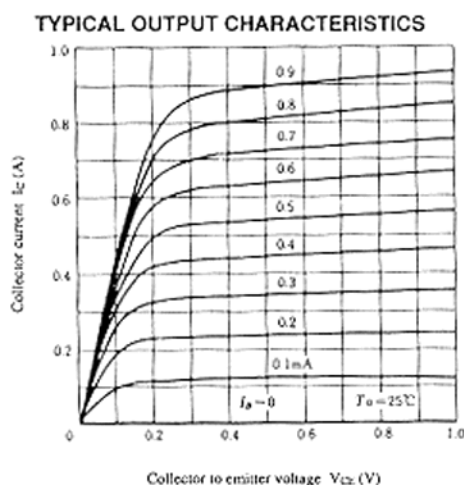
Item	Symbol	2SD2063	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	10	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	1	A
Collector peak current	$i_{C(peak)}$	2	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION
CURVE

■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	15	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	10	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5	—	—	V
Collector cutoff current	I_{CBO}	$V_{CB} = 12V, I_E = 0$	—	—	0.1	μA
	I_{CEO}	$V_{CE} = 8V, R_{BE} = \infty$	—	—	0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	—	—	0.1	μA
DC current transfer ratio	h_{FE1}	$V_{CE} = 0.3V, I_C = 0.5A^*$	400	—	2000	
	h_{FE2}	$V_{CE} = 0.3V, I_C = 1A^*$	400	—	—	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.5A, I_B = 2mA^*$	—	—	0.3	V
	$V_{CE(sat)}$	$I_C = 1A, I_B = 3mA^*$	—	—	0.33	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 0.5A, I_B = 2mA^*$	—	—	1.1	V

- Pulse Test



COLLECTOR OUTPUT CAPACITANCE VS.
COLLECTOR TO BASE VOLTAGE

